

X0060

N-Channel Enhancement Mode MOSFET

16V(VDS) / ± 12 V(VGS) / 7A(ID)

Rev0.5



Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8" wafer
X0060	16V(V_{DS}) / ± 12V(V_{GS}) / 7A(I_D) N-Channel Enhancement Mode MOSFET	55,496

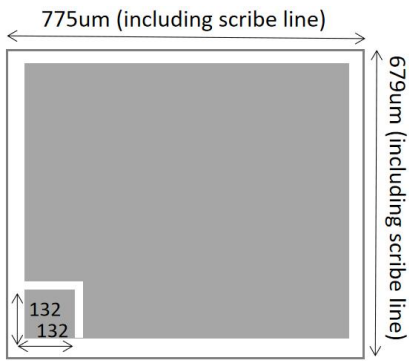
2. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (13kÅ°)
Nominal Front Metal Composition, Thickness	AlCu (4μm)
Wafer Diameter	200mm, with 010 notch
Wafer Thickness	150±10μm
Scribe Line Width	60μm
Passivation	SRO+SiN

3. Key Electrical Characteristics of Die (at T_J = 25 °C, unless otherwise specified)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	16			V	V _{GS} =0V, I _D =250μA
I _D (Device Ref)	Continuous Drain Current			7	A	T _J =25°C
R _{DS(on)} (CP)	Static Drain-to-Source On-Resistance		9	14	mΩ	V _{GS} =4.5V, I _D =1A
			13	19	mΩ	V _{GS} =2.5V, I _D =1A
R _{DS(on)} (FT)	Static Drain-to-Source On-Resistance		12	16	mΩ	V _{GS} =4.5V, I _D =7A
			16	21	mΩ	V _{GS} =2.5V, I _D =5A
V _{GS(th)}	Gate Threshold Voltage	0.5	0.75	1.1	V	V _{DS} =V _{GS} , I _D =250μA
I _{DSS}	Drain-to-Source Leakage Current			1	μA	V _{DS} =16V, V _{GS} =0V
I _{GSS}	Gate-to-Source Leakage Current			±100	nA	V _{GS} =±12V, V _{DS} =0V
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 150°C Max				

4. Die Outline

	Die Size: 775μm × 679μm (including scribe line)
	Gate: 132μm × 132μm
	For DFN2*2 package Suggest Bonding wire: Gate: 1 × 1.0 mil Cu Source: 6 × 1.7 mil Cu